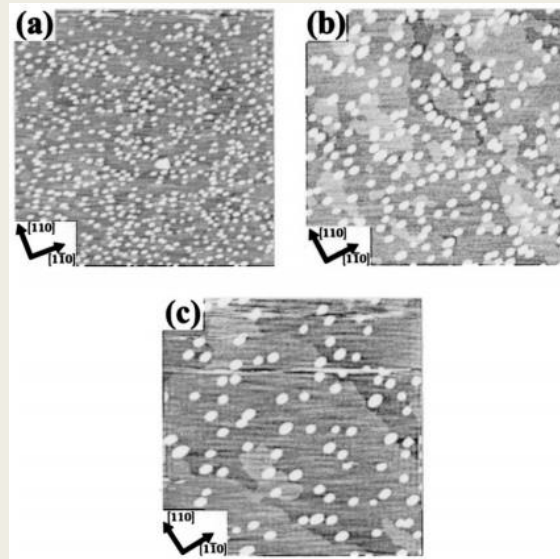


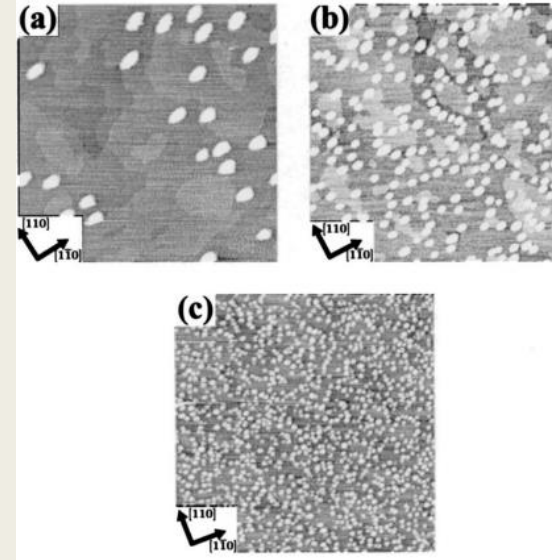
Scanning tunneling microscopy study of InAs islands grown on GaAs(001) substrates

- Growth of InAs islands and wetting layers (WLs) on GaAs(001) substrates.



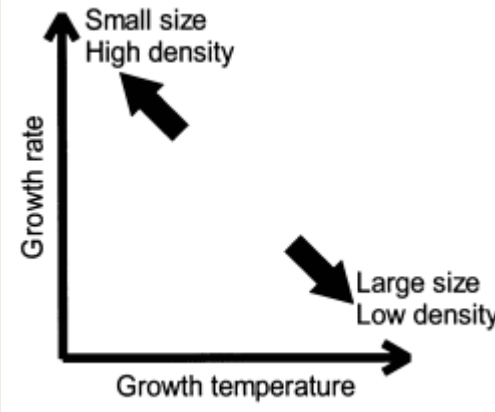
Different Temperature

- a) 420 °C ($V_s=2.0$ V, $I_t=1.0$ nA)
- b) 450 °C ($V_s=2.0$ V, $I_t=1.0$ nA)
- c) 480 °C ($V_s=2.0$ V, $I_t=2.0$ nA)



Different Grow Rate

- a) 0.025 ML/s-1 (450 °C, $V_s=2.0$ V, $I_t=1.5$ nA)
- b) 0.067 ML/s-1 (450 °C, $V_s=2.0$ V, $I_t=1.0$ nA)
- c) 0.133 ML/s-1 (450 °C, $V_s=2.5$ V, $I_t=1.0$ nA)



This figure summarizes the STM results